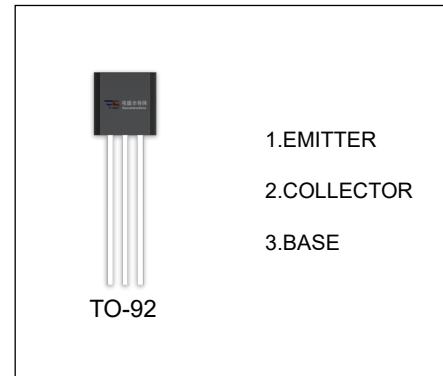


2SA1083 TRANSISTOR (PNP)

FEATURES

- Low Frequency Low Noise Amplifier



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA1083	TO-92	Bulk	1000pcs/Bag
2SA1083-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _D	Collector Power Dissipation	400	mW
R _{KJA}	Thermal Resistance from Junction to Ambient	312	°C /W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.01\text{mA}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	7A
Emitter cut-off current	I_{EBO}	$V_{EB} = -2\text{V}, I_C = 0$			-0.1	7A
DC current gain	h_{FE}	$V_{CE} = -12\text{V}, I_C = -2\text{mA}$	250		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$			-0.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = -12\text{V}, I_C = -2\text{mA}$		-0.6		V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		3.5		pF
Transition frequency	f_T	$V_{CE} = -12\text{V}, I_C = -2\text{mA}$		90		MHz

CLASSIFICATION OF h_{FE}

RANK	D	E
RANGE	250-500	400-800